TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

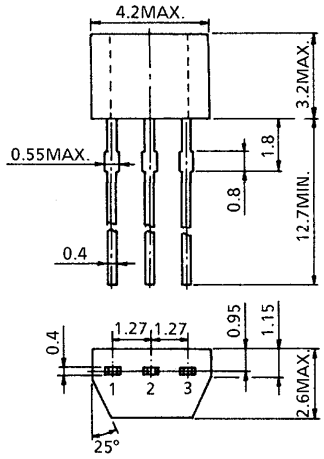
2SC3267

POWER AMPLIFIER APPLICATIONS

POWER SWICHING APPLICATIONS

- Low Saturation Voltage : $V_{CE\ (sat)}$ = 0.5V (Max.) @I_C = 2A
- Complementary to 2SA1297

Unit in mm



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC	—
EIAJ	—
TOSHIBA	2-4E1A

Weight : 0.13g

MAXIMUM RATINGS (Ta = 25°C)

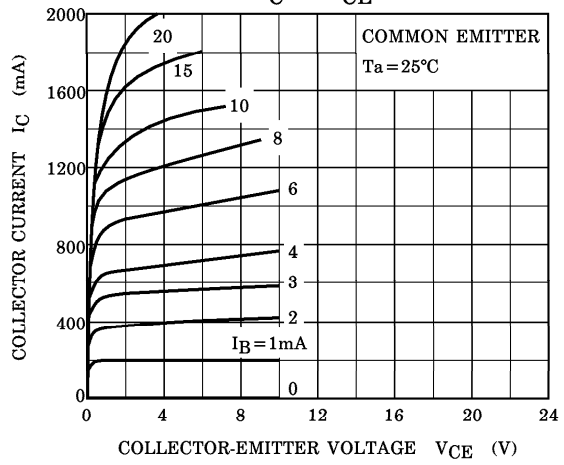
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	2	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

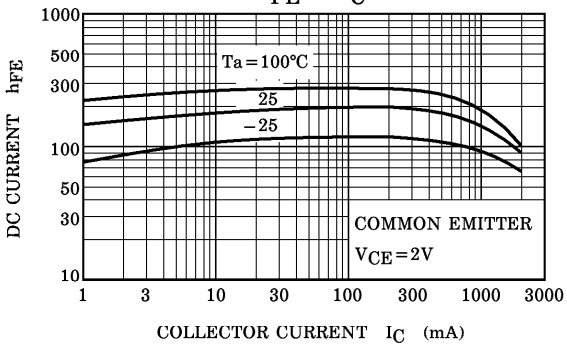
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = 20V, I_E = 0	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 6V, I_C = 0	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)\ CEO}$	I_C = 10mA, I_B = 0	20	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)\ EBO}$	I_E = 0.1mA, I_C = 0	6	—	—	V
DC Current Gain	$h_{FE\ (1)}$ (Note)	V_{CE} = 2V, I_C = 100mA	120	—	700	
	$h_{FE\ (2)}$	V_{CE} = 2V, I_C = 2A	75	—	—	
Collector-Emitter Sturation Voltage	$V_{CE\ (sat)}$	I_C = 2A, I_B = 0.1A	—	—	0.5	V
Base-Emitter Voltage	V_{BE}	V_{CE} = 2V, I_C = 0.1A	—	—	0.85	V
Transition Frequency	f_T	V_{CE} = 2V, I_C = 0.5A	—	120	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	—	30	—	pF

Note : $h_{FE\ (1)}$ Classification Y : 120~240, GR : 200~400, BL : 350~700

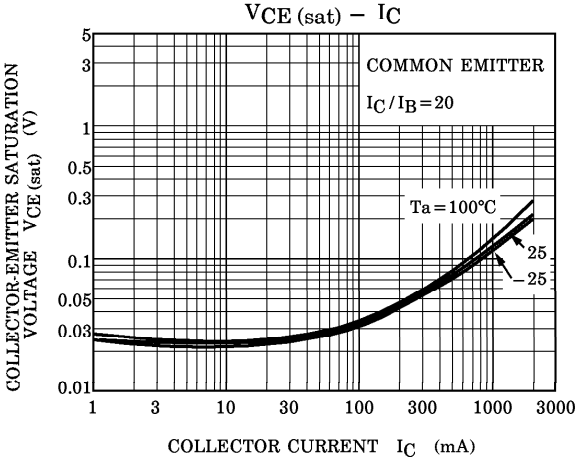
I_C – V_{CE}



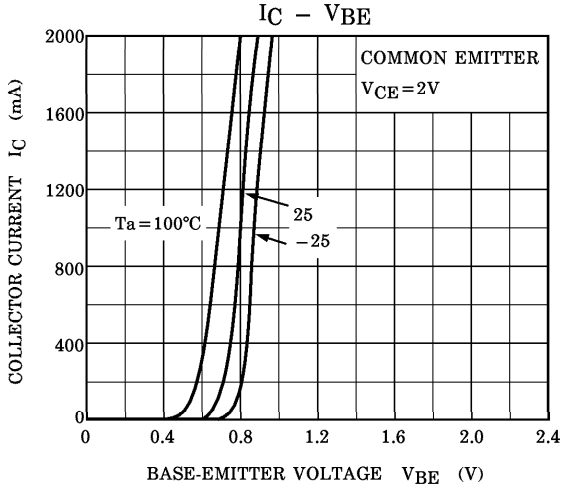
h_{FE} – I_C



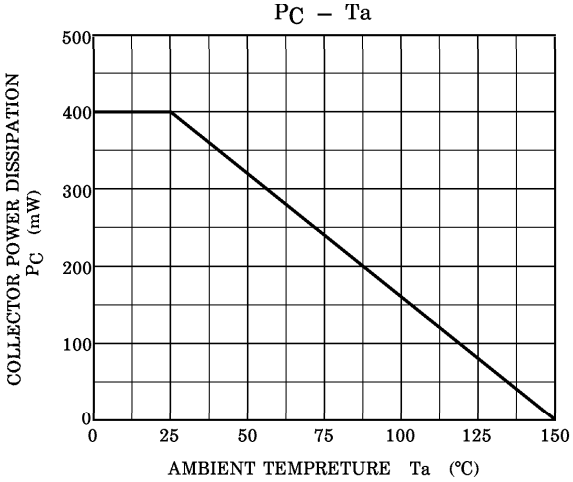
$V_{CE\,(sat)}$ – I_C



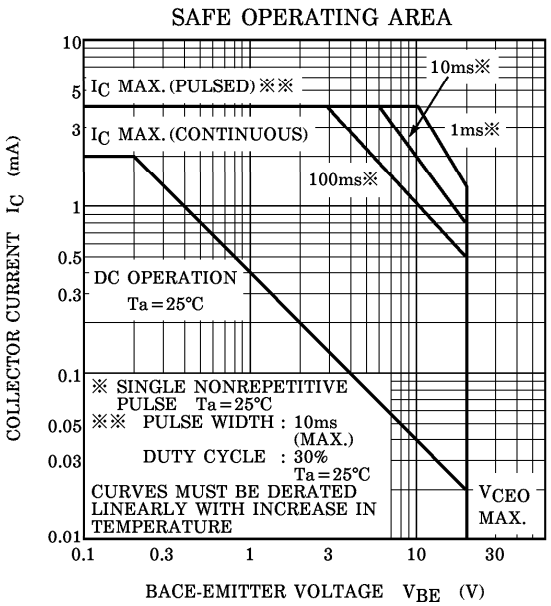
I_C – V_{BE}



P_C – Ta



SAFE OPERATING AREA



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